

NTD5406N, STD5406N

Power MOSFET

40 V, 70 A, Single N-Channel, DPAK



ON Semiconductor®

www.onsemi.com

Features

- Low $R_{DS(on)}$
- High Current Capability
- Low Gate Charge
- STD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Electronic Brake Systems
- Electronic Power Steering
- Bridge Circuits

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	40	V	
Gate-to-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current – $R_{\theta JC}$	Steady State	$T_C = 25^\circ\text{C}$	I_D	70	A
			$T_C = 125^\circ\text{C}$	40	
Power Dissipation – $R_{\theta JC}$	Steady State	$T_C = 25^\circ\text{C}$	P_D	100	W
Continuous Drain Current – $R_{\theta JA}$ (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	I_D	12.2	A
		$T_A = 125^\circ\text{C}$	7.0		
Power Dissipation – $R_{\theta JA}$ (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	P_D	3.0	W
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	I_{DM}	150	A	
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 175	$^\circ\text{C}$	
Source Current (Body Diode) Pulsed		I_S	63.5	A	
Single Pulse Drain-to-Source Avalanche Energy – ($V_{DD} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{PK} = 30 \text{ A}, L = 1 \text{ mH}, R_G = 25 \Omega$)		EAS	450	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

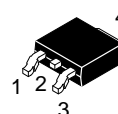
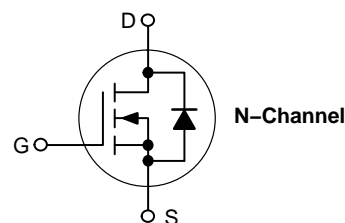
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS (Note 1)

Parameter	Symbol	Max	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	1.5	$^\circ\text{C}/\text{W}$
Junction-to-Ambient (Note 1)	$R_{\theta JA}$	49	

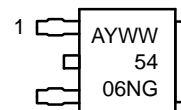
1. Surface mounted on FR4 board using 1 sq in pad size, (Cu Area 1.127 sq in [2 oz] including traces).

$V_{(BR)DSS}$	$R_{DS(ON)}$ TYP	I_D MAX (Note 1)
40 V	8.7 m Ω @ 10 V	70 A



DPAK
CASE 369C
STYLE 2

MARKING DIAGRAM



A = Assembly Location*
Y = Year
WW = Work Week
5406N = Specific Device Code
G = Pb-Free Device

* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

ORDERING INFORMATION

Device	Package	Shipping†
NTD5406NT4G	DPAK (Pb-Free)	2500 / Tape & Reel
STD5406NT4G*	DPAK (Pb-Free)	2500 / Tape & Reel
STD5406NT4G-VF01	DPAK (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTD5406N, STD5406N

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			42		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 40 V	T _J = 25°C		1.0	μA
			T _J = 100°C		10	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±30 V			±100	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	1.5		3.5	V
Gate Threshold Temperature Coefficient	V _{GS(TH)} /T _J			-7.0		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A		8.7	10	mΩ
		V _{GS} = 5.0 V, I _D = 10 A		13.2	17	
Forward Transconductance	g _{FS}	V _{GS} = 10 V, I _D = 10 A		19		S

CHARGES AND CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 32 V		1375	2500	pF
Output Capacitance	C _{OSS}			370	700	
Reverse Transfer Capacitance	C _{RSS}			160	300	
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 32 V, I _D = 30 A		45		nC
Threshold Gate Charge	Q _{G(TH)}			2.0		
Gate-to-Source Charge	Q _{GS}			5.4		
Gate-to-Drain Charge	Q _{GD}			20		

SWITCHING CHARACTERISTICS, V_{GS} = 10 V (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 10 V, V _{DD} = 32 V, I _D = 30 A, R _G = 2.5 Ω		7.2		ns
Rise Time	t _r			57		
Turn-Off Delay Time	t _{d(OFF)}			30		
Fall Time	t _f			67		

SWITCHING CHARACTERISTICS, V_{GS} = 5 V (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 5.0 V, V _{DD} = 20 V, I _D = 30 A, R _G = 2.5 Ω		15		ns
Rise Time	t _r			147		
Turn-Off Delay Time	t _{d(OFF)}			20		
Fall Time	t _f			29		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 10 A	T _J = 25°C		0.82	1.1	V
			T _J = 125°C		0.67		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _{SD} /dt = 100 A/μs, I _S = 10 A		46		ns	
Charge Time	t _a			24			
Discharge Time	t _b			22			
Reverse Recovery Charge	Q _{RR}			65			nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

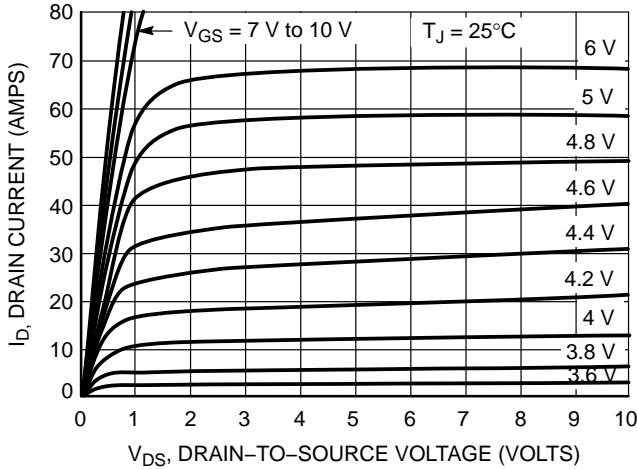


Figure 1. On-Region Characteristics

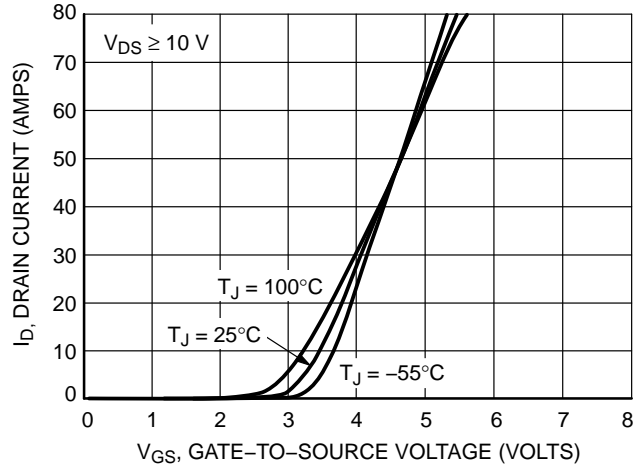


Figure 2. Transfer Characteristics

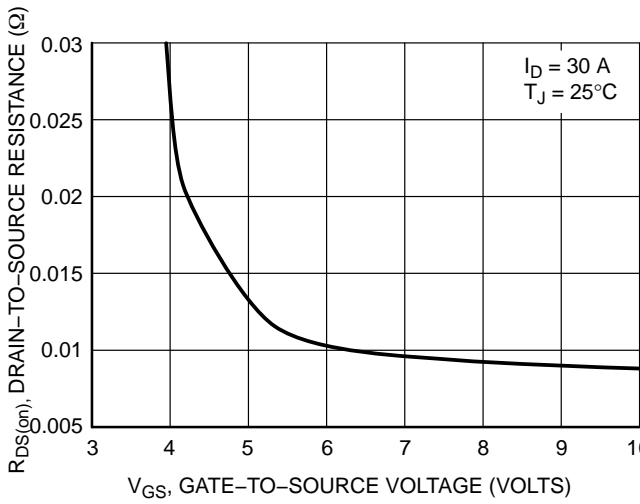


Figure 3. On-Resistance vs. Gate-to-Source Voltage

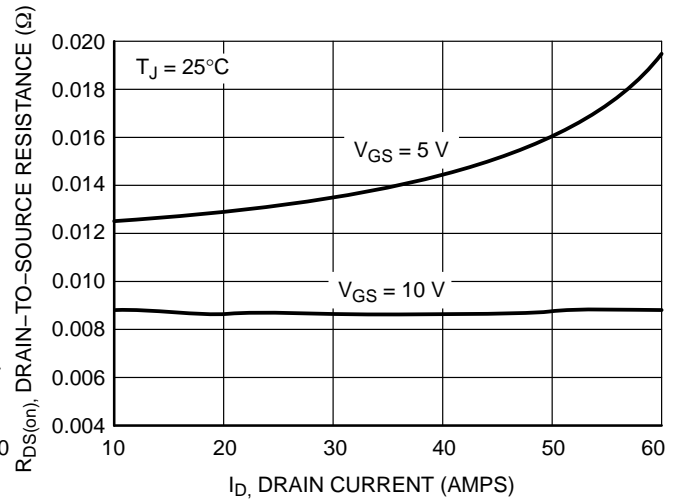


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

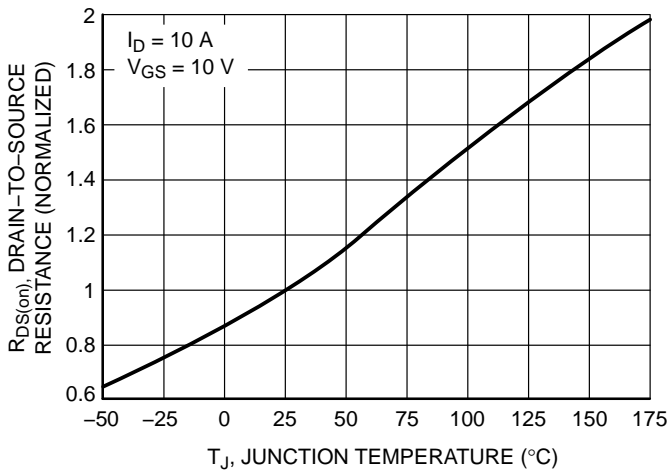


Figure 5. On-Resistance Variation with Temperature

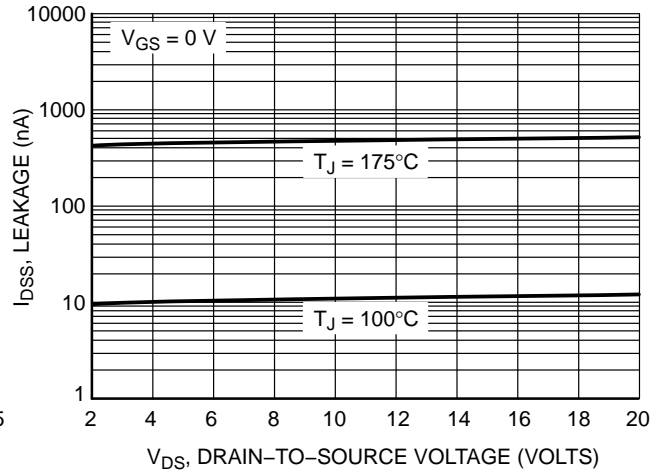


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTD5406N, STD5406N

TYPICAL PERFORMANCE CURVES

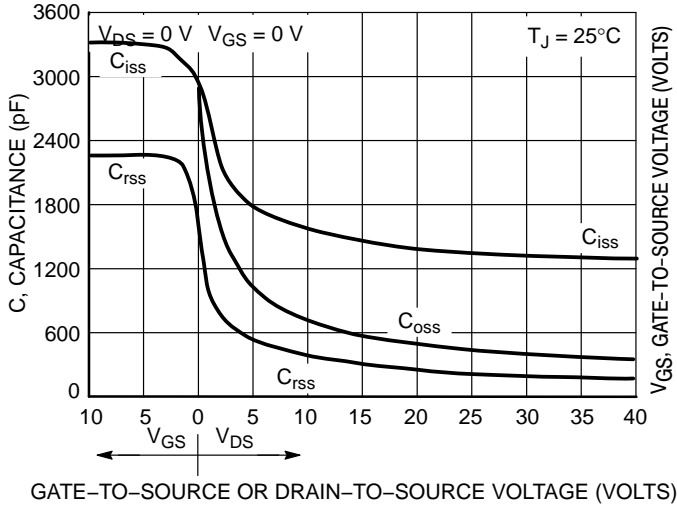


Figure 7. Capacitance Variation

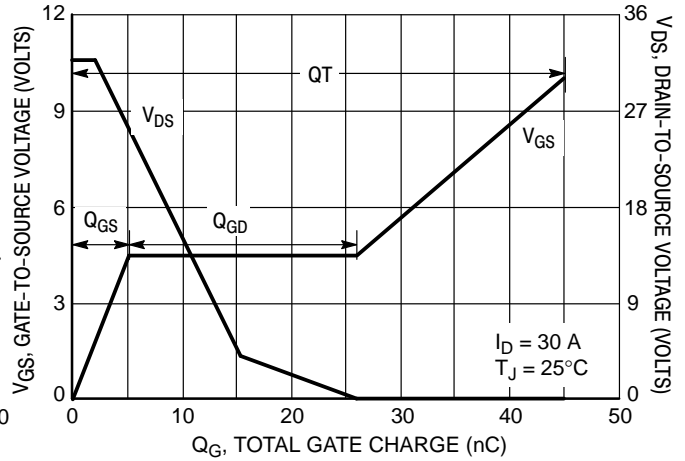


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

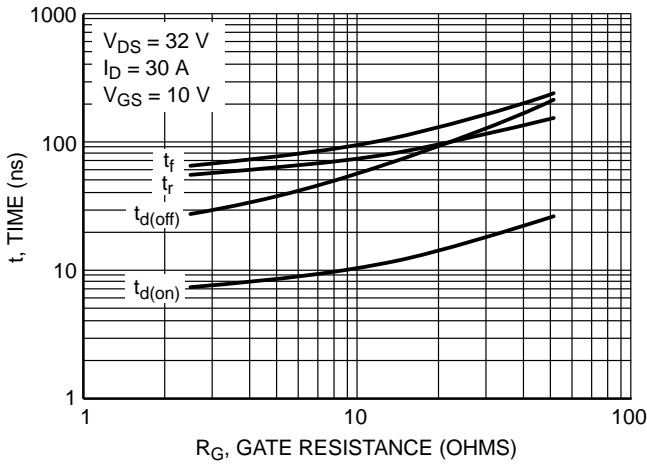


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

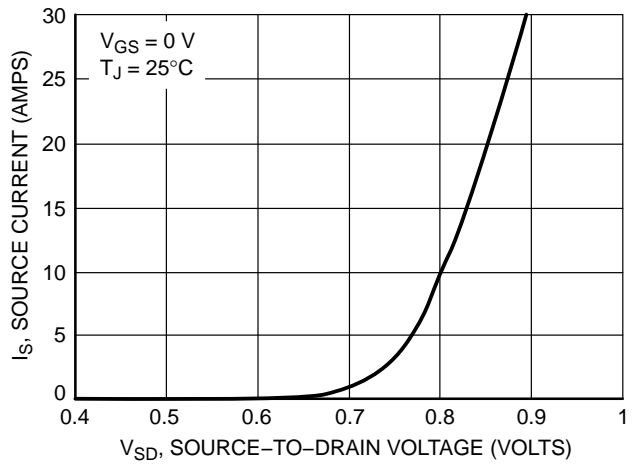


Figure 10. Diode Forward Voltage vs. Current

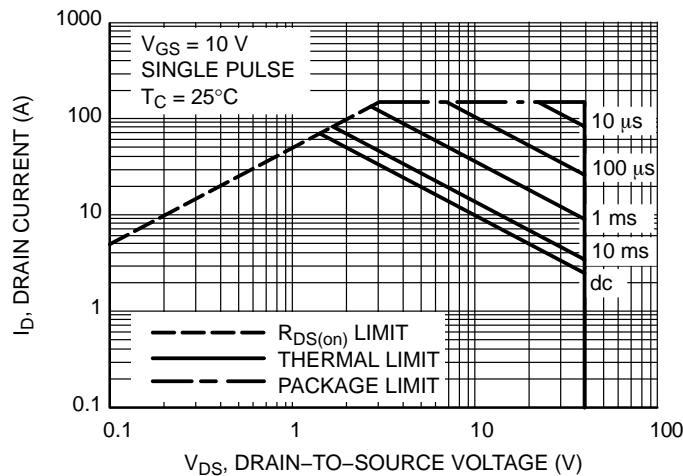


Figure 11. Maximum Rated Forward Biased Safe Operating Area

NTD5406N, STD5406N

TYPICAL PERFORMANCE CURVES

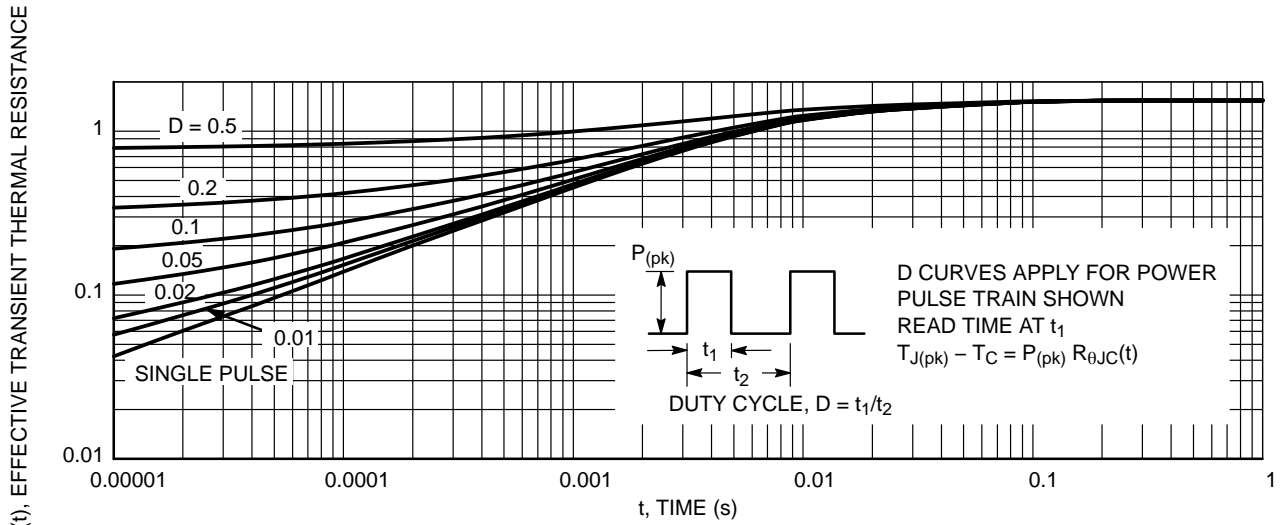


Figure 12. Thermal Response

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales